

### General Description

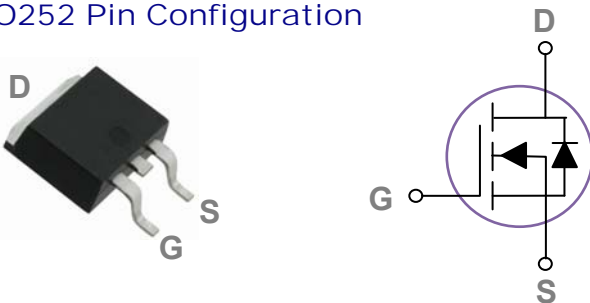
These N-Channel enhancement mode power field effect transistors are using Super Junction technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply

BVDSS	RDS(ON)	ID
700V	0.93Ω	4A

### Features

- 4A, 700V,  $R_{DS(ON)} = 0.93\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### TO252 Pin Configuration



### Applications

- High efficient switched mode power supplies
- LED Lighting
- Adapter/charger

### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	700	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current – Continuous ( $T_c=25^\circ\text{C}$ )	4	A
	Drain Current – Continuous ( $T_c=100^\circ\text{C}$ )	2.5	A
$I_{DM}$	Drain Current – Pulsed (Note 1)	12	A
EAS	Single Pulse Avalanche Energy (Note 2)	45	mJ
IAS	Single Pulse Avalanche Current (Note 2)	3	A
$P_D$	Power Dissipation ( $T_c=25^\circ\text{C}$ )	50	W
	Power Dissipation – Derate above $25^\circ\text{C}$	0.4	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	2.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	700	---	---	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=700V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{DS}=700V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	10	---	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	$\pm 100$	nA

**On Characteristics**

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=2A$	---	0.83	0.93	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	2.5	3.5	4.5	V

**Dynamic and switching Characteristics**

$Q_g$	Total Gate Charge (10V)	$V_{DS}=480V, V_{GS}=10V, I_D=2A$ (Note 4,5)	---	13	20	nC
$Q_{gs}$	Gate-Source Charge		---	3	6	
$Q_{gd}$	Gate-Drain Charge		---	6	12	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=300V, V_{GS}=10V, R_G=12\Omega,$ $I_D=2A$ (Note 4,5)	---	13	20	ns
$T_r$	Rise Time		---	12	19	
$T_{d(off)}$	Turn-Off Delay Time		---	31	50	
$T_f$	Fall Time		---	9	17	
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1\text{MHz}$	---	450	700	pF
$C_{oss}$	Output Capacitance		---	300	450	
$C_{rss}$	Reverse Transfer Capacitance		---	5	10	

**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	4	A
$I_{SM}$	Pulsed Source Current		---	---	8	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=2A, T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_S=4A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	220	---	ns
$Q_{rr}$	Reverse Recovery Charge	(Note 4)	---	1.6	---	$\mu C$

**Note :**

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2.  $V_{DD}=50V, V_{GS}=10V, L=10\text{mH}, I_{AS}=3A, R_G=1.46\Omega$ , Starting  $T_J=25^\circ\text{C}$ .
3.  $I_{SD} \leq 2A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$ .
4. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. Essentially independent of operating temperature.

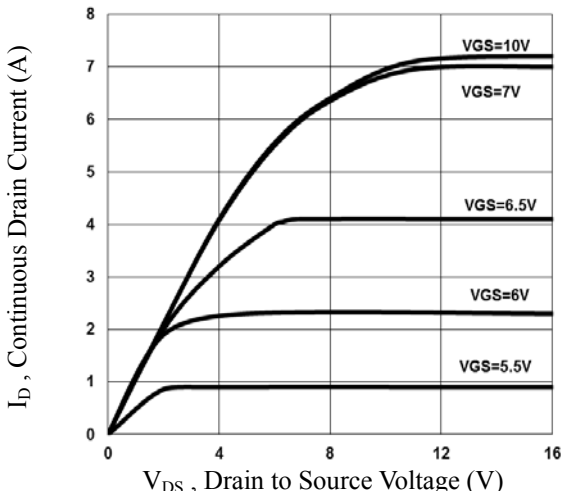


Fig.1 Output Characteristics

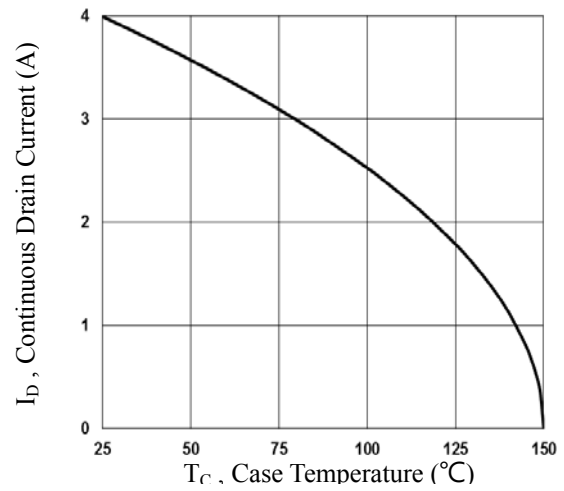


Fig.2 Continuous Drain Current vs.  $T_C$

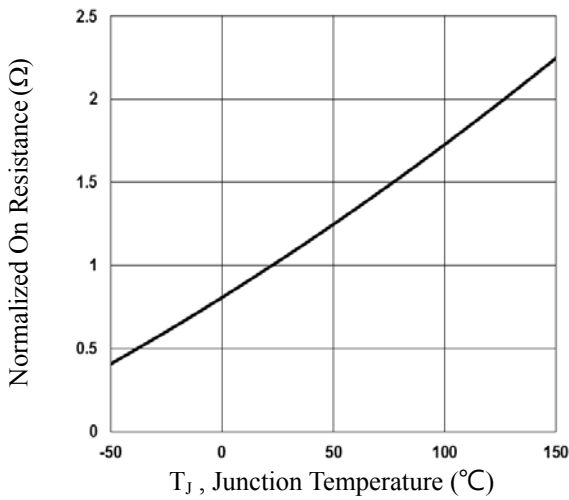


Fig.3 Normalized  $R_{DS(on)}$  vs.  $T_J$

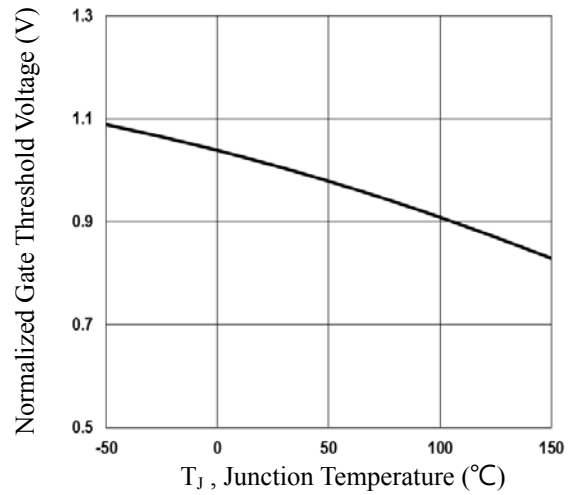


Fig.4 Normalized  $V_{th}$  vs.  $T_J$

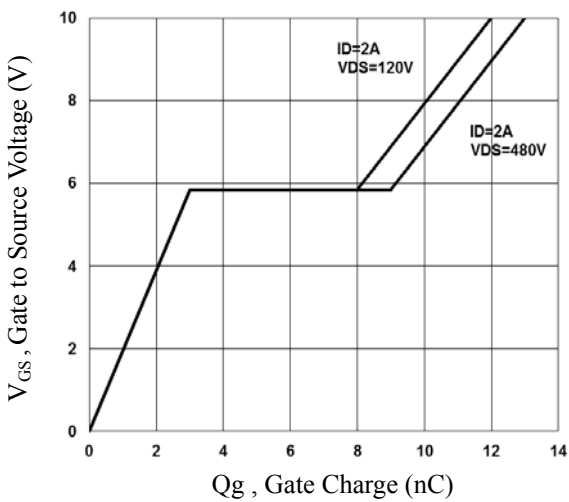


Fig.5 Gate Charge Waveform

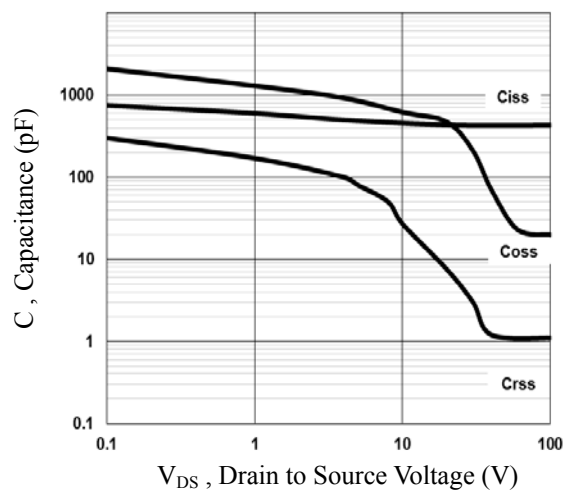


Fig.6 Capacitance Characteristics

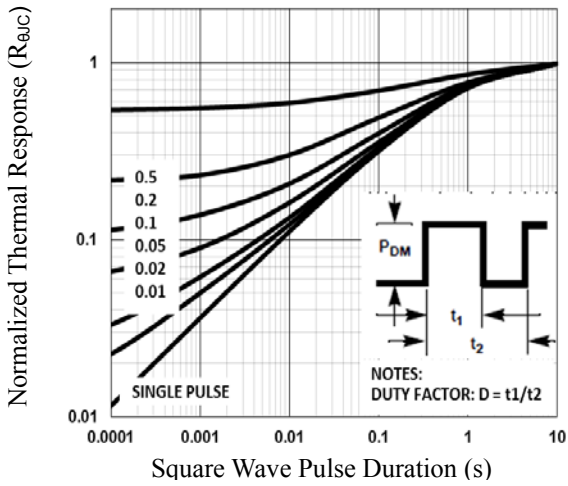


Fig.7 Normalized Transient Impedance

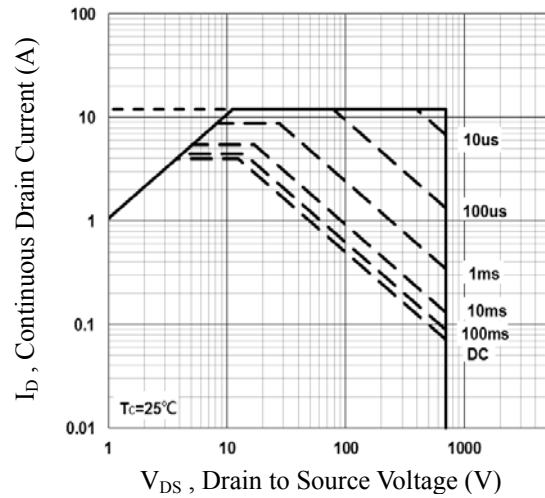


Fig.8 Maximum Safe Operation Area

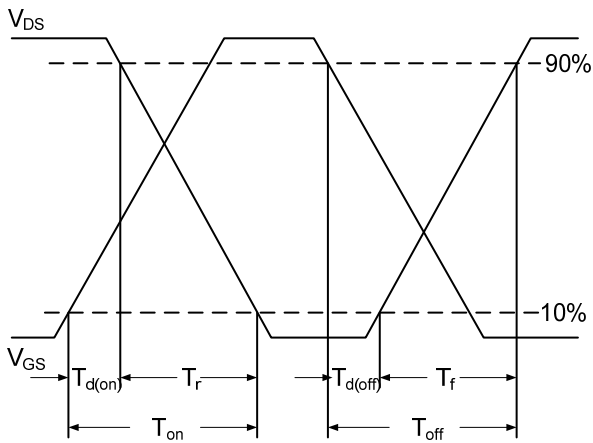


Fig.9 Switching Time Waveform

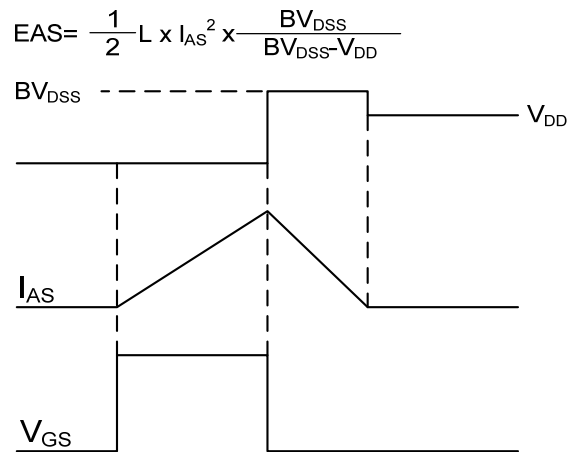
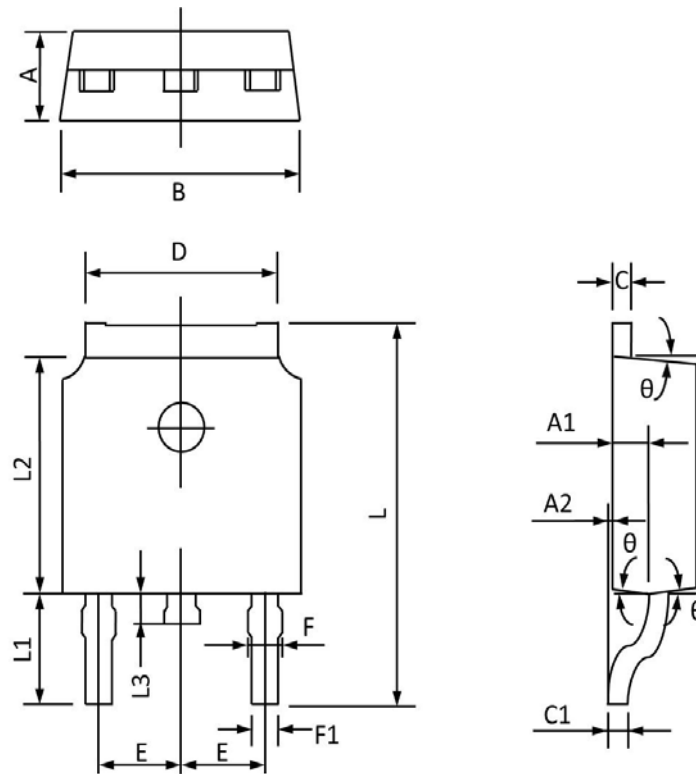


Fig.10 EAS Waveform

## TO252 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	2.400	2.200	0.094	0.087
A1	1.110	0.910	0.044	0.036
A2	0.150	0.000	0.006	0.000
B	6.800	6.400	0.268	0.252
C	0.580	0.450	0.023	0.018
C1	0.580	0.460	0.023	0.018
D	5.500	5.100	0.217	0.201
E	2.386	2.186	0.094	0.086
F	0.940	0.600	0.037	0.024
F1	0.860	0.500	0.034	0.020
L	10.400	9.400	0.409	0.370
L1	3.000	2.400	0.118	0.094
L2	6.200	5.400	0.244	0.213
L3	1.200	0.600	0.047	0.024
$\theta$	9°	3°	9°	3°